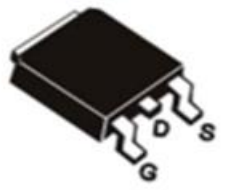
FMD3N60E5 N-CHANNEL POWER MOSFET

Features :

- Fast body diode eliminates the need for external diode in ZVS applications.
- Lower Gate charge results in simpler drive requirements
- Higher Gate voltage threshold offers improved noise Immunity
- Low on-resistance
- RoHS compliant

V_{DSS}	600	V
I_D	3	A
Trr	85	ns
$R_{DS(ON)Typ}$	2.6	Ω



TO-252T

Applications:

- Motor Control applications
- Uninterruptible Power Supplies
- Zero Voltage Switching SMPS

Absolute（Tc= 25℃）:

Symbol	Parameter	Rating	Units
V_{DSS}	Drain-to-Source Voltage	600	V
I_D	Continuous Drain Current	3*	A
	Continuous Drain Current T_C = 100 °C	1.95*	A
I_{DM}①	Pulsed Drain Current	12*	A
V_{GS}	Gate-to-Source Voltage	±30	V
E_{AS}②	Single Pulse Avalanche Energy	157	mJ
E_{AR}①	Avalanche Energy,Repititive	15	mJ
I_{AR}①	Avalanche Current	1.7	A
P_D	Power Dissipation	54	W
dv/dt	Peak Diode Recovery dv/dt	5	V/nS
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	–55 to 150	℃

*Drain current limited by maximum junction temperature

Ordering Information

Product number	Package	Marking	Packing	Quantity
FMD3N60E5	TO252T	FMD3N60E5	Tape & Reel	2500

Electronic Characteristics（Tc=25°C）

PARAMETER	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Drain-source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=250μA	600			V
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta Tj$	I_D=250uA, Referenced to 25°C		0.6		V/°C
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS}=V_{DS}, I_D=250μA	2.0		4.0	V
Drain-source Leakage Current	I_{DSS}	V_{DS} =600V,V_{GS} =0V, Tj=25°C			1	μA
		V_{DS} =480V,V_{GS} =0V, Tj=125°C			100	μA
Forward Transconductance	gfs	V_{DS} =15V, I_D=1.5A ③		2.6		S
Gate-body Leakage Current	I_{GSS}	V_{DS} =0V,V_{GS} =±30V			±100	nA
Drain-source On Resistance	$R_{DS(ON)}$	V_{GS} =10V, I_D=1.5A ③		2.6	3.2	Ω
Input Capacitance	Ciss	V_{GS} = 0V, V_{DS} = 25V F = 1.0MHZ		430		pF
Output Capacitance	Coss			42		
Reverse transfer Capacitance	Crss			6		
Turn-on Delay Time	Td(on)	V_{DD}=300V, I_D =3.0A R_G=25Ω ③		10		ns
Rise Time	Tr			9		
Turn -Off Delay Time	Td(off)			35		
Fall Time	Tf			10		
Total Gate Charge	Qg	I_D =3.0A, V_{DS} = 480V V_{GS} = 10V ③		10.9		nC
Gate-to-Source Charge	Qgs			3.4		nC
Gate-to-Drain Charge	Qgd			1.7		nC
Continuous Diode Forward Current	I_S				3.0	A
Max Pulsed Diode Forward Current	I_{SM}				12	A
Diode Forward Voltage	V_{SD}	Tj=25°C, Is=3.0A,V_{GS} =0V ③			1.4	V
Reverse Recovery Time	trr	Tj=25°C, If=3.0A di/dt=100A/μs ③		84.6		ns
Reverse Recovery Charge	Qrr			0.2		uC
Thermal Resistance Junction-case	Rth_{JC}			2.31		℃/W
Thermal Resistance Junction-ambient	Rth_{JA}			62.5		℃/W

Notes:

① Repetitive rating: Pulse width limited by maximum junction temperature

② Starting Tj=25°C, V_{DD} =50V, L=36mH, R_G =25Ω, I_{AS}=3.0A

③ Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%

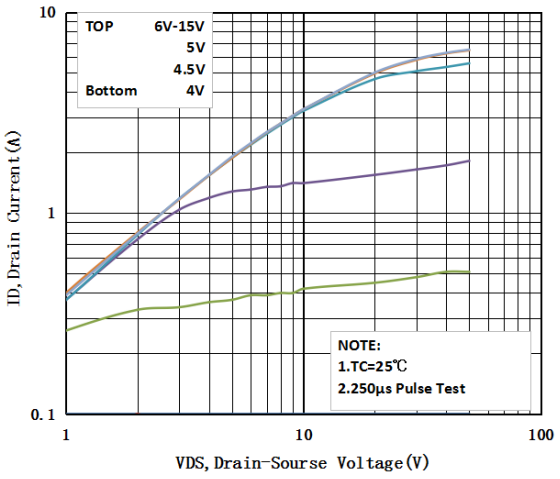


Fig1 Typical Output Characteristics, Tc=25℃

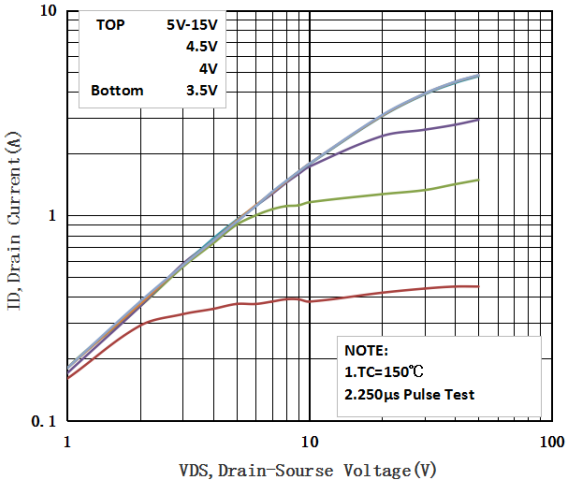


Fig2 Typical Output Characteristics, Tc=150℃

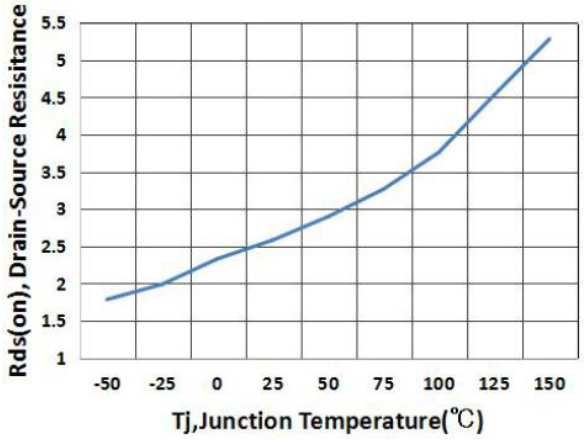


Fig3 On-Resistance Vs.Temperature

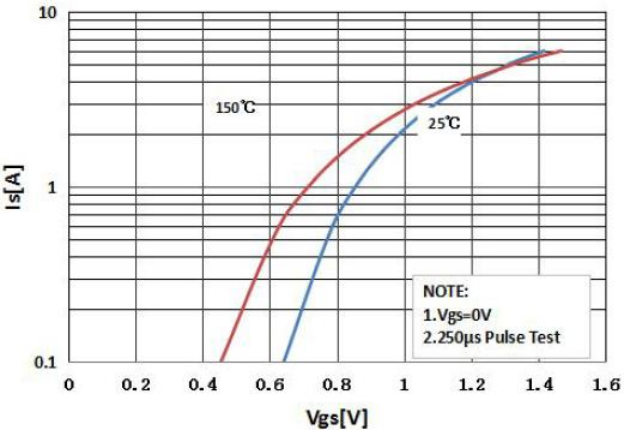


Fig4 Typical Source-Drain Diode Forward Voltage

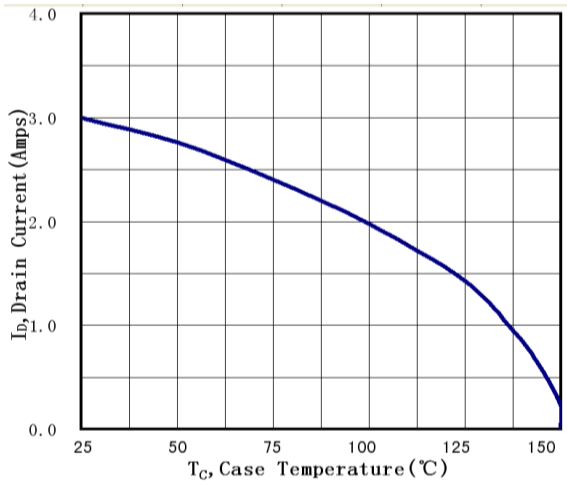


Fig5 Maximum Drain Current Vs.Case Temperature

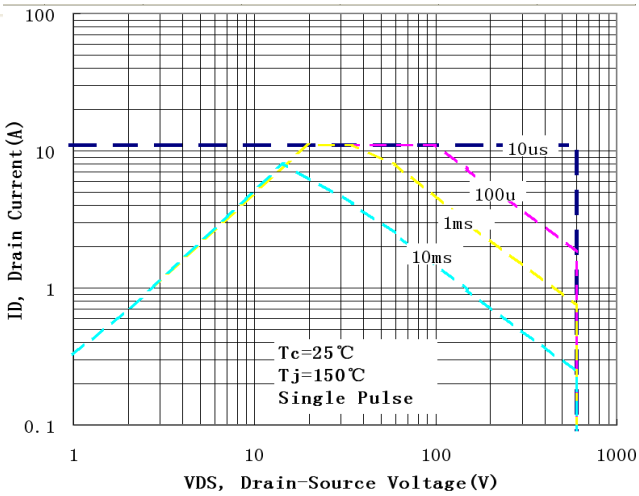


Fig6 Maximum Safe Operating Area

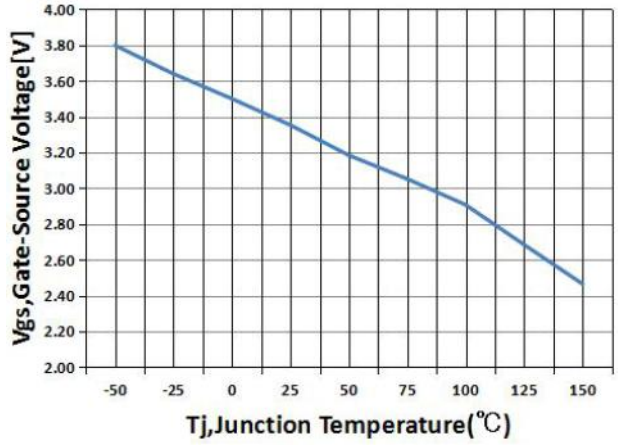


Fig7 Gate Threshold Voltage Variation vs.Temperature

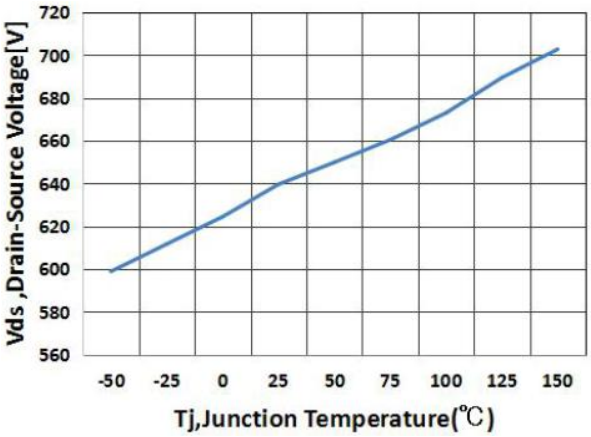


Fig8 Breakdown Voltage Variation vs.Temperature

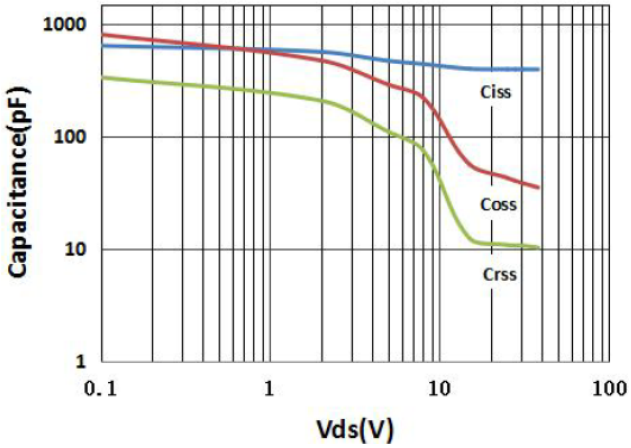


Fig9 Capacitance Characteristics

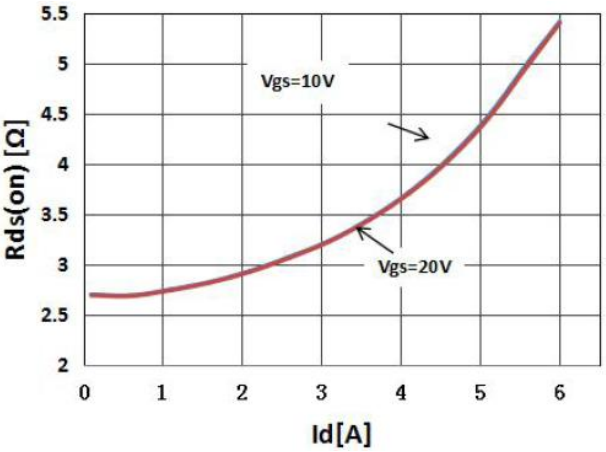


Fig10 On-Resistance Variation VS. Drain Current and Gate Voltage

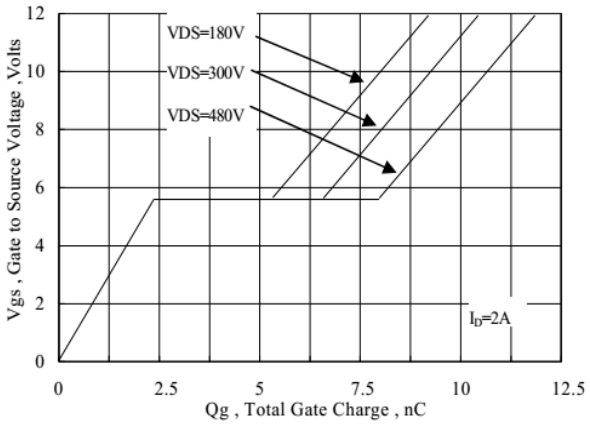


Fig11 Gate Charge VS Gate to Source Volitage

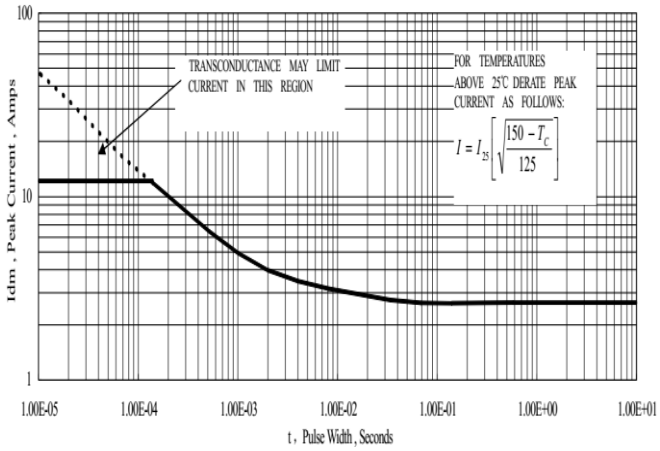


Fig12 I_{DM} VS Pulse Width

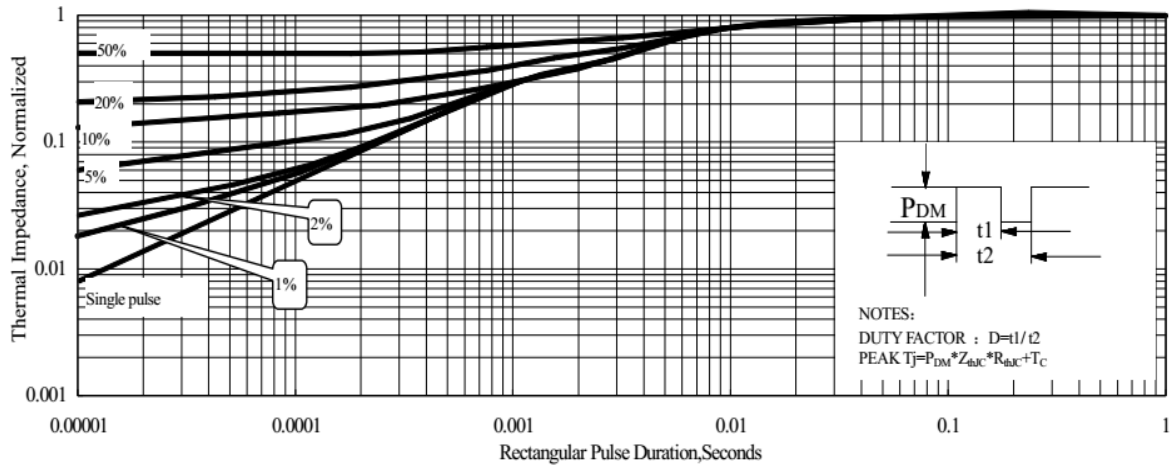
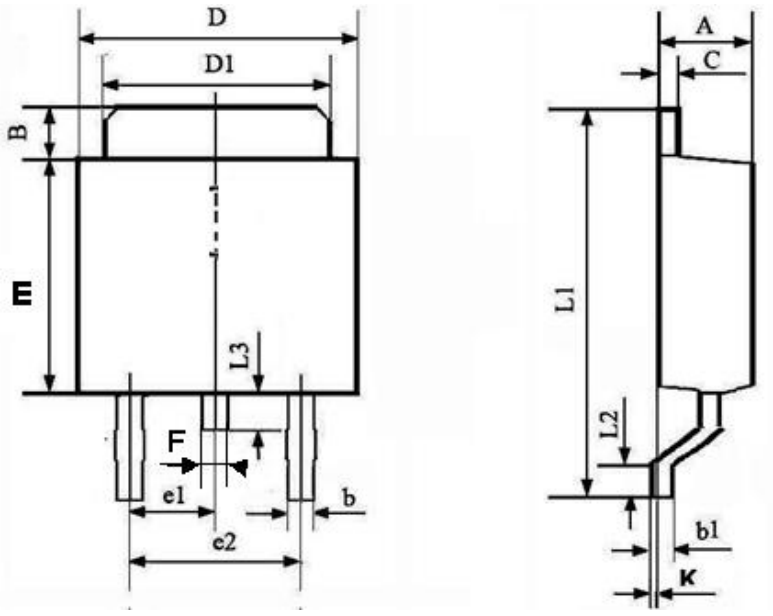


Fig13 Normalized Thermal Impendance VS Rectangular Pulse Duration

TO-252T MECHANICAL DATA

UNIT：mm

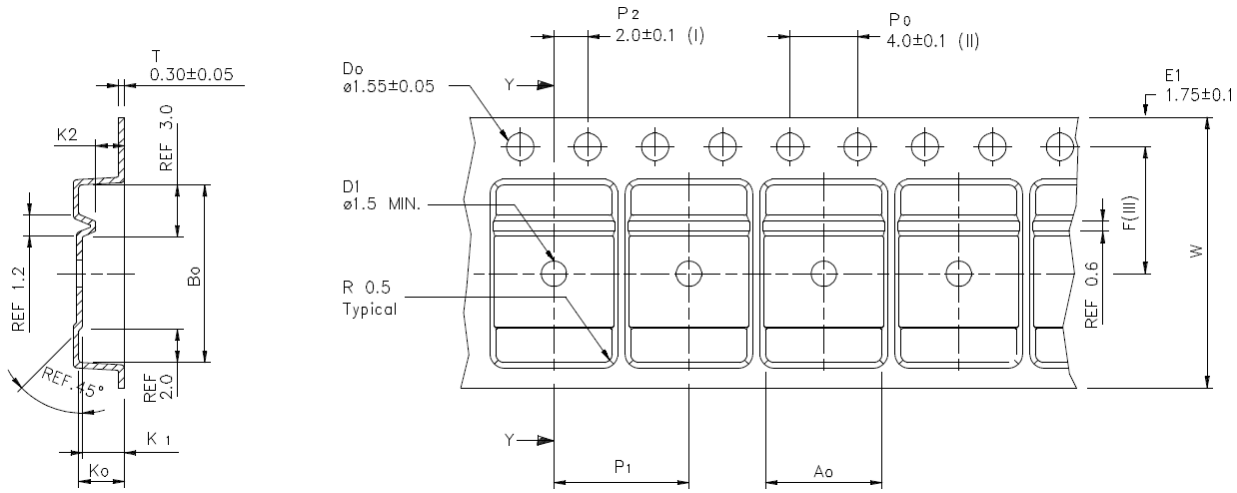
SYMBOL	min	max	SYMBOL	min	max
A	2.20	2.40	B	0.85	1.25
b	0.50	0.80	C	0.45	0.70
b1	0.45	0.70	D	6.30	6.70
D1	5.10	5.50	E	5.30	6.20
L1	9.20	10.60	F	0.50	0.90
L2	0.90	1.50	e1	2.25	2.35
L3	0.60	1.10	e2	4.50	4.70
			K	0.00	0.18



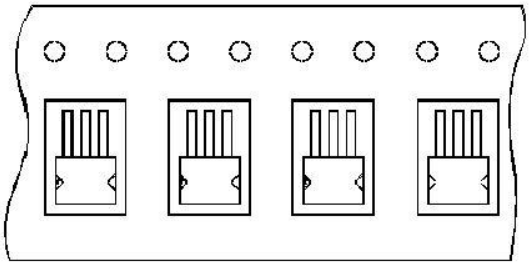
TO-252T TAPE AND REEL DATA

UNIT：mm

SYMBOL	min	nom	max	SYMBOL	min	nom	max
A0	6.80	6.90	7.00	B0	10.40	10.50	10.60
K0	2.60	2.70	2.90	K1	2.40	2.50	2.60
F	7.40	7.50	7.60	K2	1.60	1.70	1.80
W	15.90	16.00	16.10	P1	7.90	8.00	8.10



USER DIRECTION OF FEED



UNIT ORIENTATION

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